

KSP2222

General Purpose Transistor

- Collector-Emitter Voltage: V_{CEO}= 30V
 Collector Dissipation: P_C (max)=625mW



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|---------------------------|-----------|-------|
| V_{CBO} | Collector-Base Voltage | 60 | V |
| V _{CEO} | Collector-Emitter Voltage | 30 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| I _C | Collector Current | 600 | mA |
| P _C | Collector Dissipation | 625 | mW |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C |

Electrical Characteristics T_a =25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--|--|-----------------------------|------|------------|--------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_{C}=10\mu A, I_{E}=0$ | 60 | | | V |
| BV _{CEO} | Collector Emitter Breakdown Voltage | I _C =10mA, I _B =0 | 30 | | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | I _E =10μA, I _C =0 | 5 | | | V |
| I _{CBO} | Collector Cut-off Current | V_{CB} =50V, I_E =0 | | | 10 | nA |
| h _{FE} | DC Current Gain | V _{CE} =10V, I _C =0.1mA V _{CE} =10V, I _C =1mA V _{CE} =10V, I _C =10mA V _{CE} =10V, *I _C =150mA V _{CE} =10V, *I _C =500mA | 35 50 75 100 30 | | 300 | |
| V _{CE} (sat) | * Collector-Emitter Saturation Voltage | I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA | | | 0.4 1.6 | V |
| V _{BE} (sat) | * Base Emitter Saturation Voltage | I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA | | | 1.3 2.6 | V V |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0, f=1MHz | | | 8 | pF |
| f _T | Current Gain Bandwidth Product | V _{CE} =20V, I _C =20mA f=100MHz | 250 | | | MHz |
| t _{ON} | Turn On Time | V _{CC} =30V, V _{BE(off)} =0.5V I _C =150mA, I _{B1} =15mA | | 35 | ns | |
| t _{OFF} | Turn Off Time | V _{CC} =30V, I _C =150mA 289 I _{B1} =I _{B2} =15mA | | 285 | ns | |

^{*} Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

Typical Characteristics

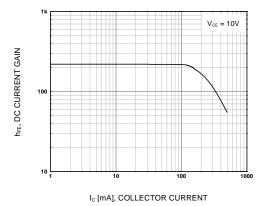


Figure 1. DC current Gain

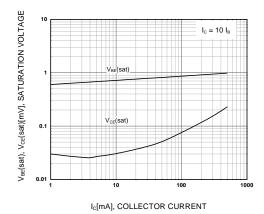


Figure 2. Collector-Emitter Saturation Voltage

Collector-Emitter Saturation Voltage

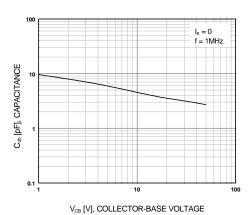


Figure 3. Collector Output Capacitance

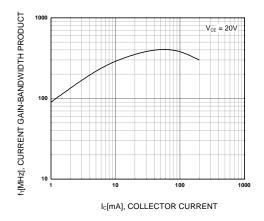
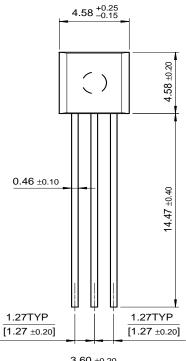
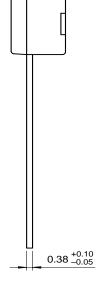
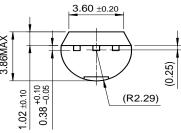


Figure 4. Current Gain Bandwidth Product

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